

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Fechko et al.

Group Art Unit: 1765

Serial No.: 10/628,188 Filed: July 28, 2003

For: REDUCING

REDUCING NITROGEN CONTENT IN SILICON

CARBIDE CRYSTALS BY SUBLIMATION GROWTH

IN A HYDROGEN-CONTAINING AMBIENT

April 30, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT CITATION UNDER 37 C.F.R. 1.97

Sir:

Attached is a list of documents on Forms PTO/SB/08A and PTO/SB/08B together with a copy of the non-patent literature documents and foreign documents. It is requested that the Examiner consider the listed U.S. issued patents and the enclosed documents and officially make them of record in accordance with the provisions of 37 C.F.R. § 1.97 and MPEP § 609.

Respectfully submitted,

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021176

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CERTIFICATE OF MAILING

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April 30, 2004.

Philip Summa

PTO/SB/08a (08-03) Approved for use through 07/31/2006. OMB 0651-0031

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Substitute for form

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

 Complete if Known

 Application Number
 10/628,188

 Filing Date
 July 28, 2003

 First Named Inventor
 Fechko et al.

 Art Unit
 1765

 Examiner Name
 Image: Complete if Known

(Use as many sheets as necessary)

Sheet 1 of 2 Attorney Docket Number 5000.302

			U.S. PATENT	DOCUMENTS	
Examiner nitials*	Cite No. ¹	Document Number Number-Kind Code ² (# known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	^{US-} 6,218,680	04-17-2001	Carter, Jr. et al.	
	2	^{US-} 6,201,342	03-13-2001	Hobart et al.	
	3	^{US-} 6,113,451	09-05-2000	Hobart et al.	
	4	^{US-} 5,709,745	01-20-1998	Larkin et al.	
	5	^{US-} 5,611,955	03-18-1997	Barrett et al.	
	6	^{US-} RE 34,861	02-14-1995	Davis et al.	
	7	^{US-} 5,119,540	06-09-1992	Kong et al.	
		US-			

FOREIGN PATENT DOCUMENTS						
Examiner	Cite	Foreign Patent Document	Publication Date Name of Patentee or	Pages, Columns, Lines,	-6	
Initials*	No.¹	Country Code ³ Number ⁴ Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Where Relevant Passages or Relevant Figures Appear	<u>'</u>
	8	EP 0 561 462 A2	09-22-1993	Philips Electronics		
•••••••	9	WO 97/28297 A1	08-07-1997	Cree Research, Inc.		
***************************************	10	WO 90/00817 A1	01-25-1990	Raychem Limited		
••••••	***************************************	***************************************		<u></u>	**************************************	
*************************	·····			•)-HEDDALUMINATION	

Examiner	Date	
Signature	Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

PTO/SB/08b (08-03)

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Complete if Known Substitute for form 1449B/PT Application Number 10/628,188 INFORMATION DISCLOSURE Filing Date July 28, 2003 First Named Inventor STATEMENT BY APPLICANT Fechko et al. Art Unit 1765 (Use as many sheets as necessary) Examiner Name Attorney Docket Number Sheet of 5000.302 2

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
	11	T. FURUSHO ET AL.; Crystal growth of silicon carbide in hydrogen atmosphere by sublimation close space technique; Journal of Crystal Growth (2002); Vol. 237-239; pages 1235-1238; Elsevier Science B.V.	
	12	S.K. LILOV ET AL.; Studies of Growth Processes in Silicon Carbide Epitaxial Layers from the Vapour Phase; Journal of Crystal Growth (1976); Vol. 32; pages 170-178; North-Holland Publishing Company	284500000
	13	I.G. IVANOV ET AL.; Nitrogen doping concentration as determined by photoluminescence in 4H- and 6H- SiC; Journal of Applied Physics; September 15, 1996; Vol. 80, No. 6; pages 3504-3508; American Institute of Physics	A244
	14	PETER RABACK ET AL.; Thermodynamic Considerations of the Role of Hydrogen in Sublimation Growth of Silicon Carbide; Journal of Electrochem. Soc.; March 1997; Vol. 144, No. 3; pages 1024-1027; The Electrochemical Society, Inc.	4114111111
			4585*****

Considered		Date	Examiner
(Signature Considered	l	Considered	Signature

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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